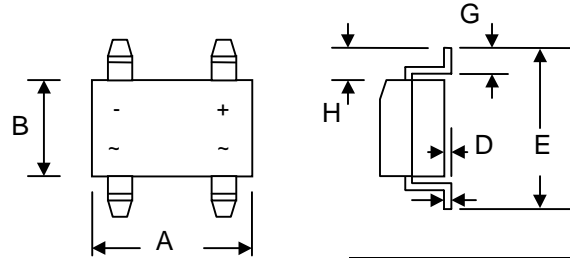


1.0A SUPER FAST SURFACE MOUNT GLASS PASSIVATED BRIDGE RECTIFIER

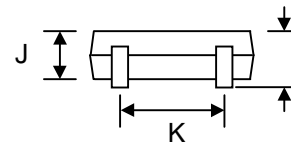
Features

- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Surge Current Capability
- Designed for Surface Mount Application
- Plastic Material – UL Flammability 94V-O



Mechanical Data

- Case: MB-F, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Case
- Weight: 0.134 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- **Lead Free: For RoHS / Lead Free Version**



MB-F		
Dim	Min	Max
A	4.50	4.95
B	3.60	4.10
C	0.15	0.35
D	—	0.20
E	6.40	7.00
G	0.50	1.10
H	1.30	1.70
J	1.20	1.60
K	2.30	2.70
L	—	1.80
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	EMB1F	EMB2F	EMB4F	EMB6F	Unit
Peak Repetitive Reverse Voltage	V _{RRM}					
Working Peak Reverse Voltage	V _{RWM}	100	200	400	600	V
DC Blocking Voltage	V _R					
RMS Reverse Voltage	V _{R(RMS)}	70	140	280	560	V
Average Rectified Output Current (Note 1) @T _A = 40°C	I _O	1.0				A
Average Rectified Output Current (Note 2) @T _A = 40°C						
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	35				A
I ² t Rating for Fusing (t < 8.3ms)	I ² t	5.0				A ² s
Forward Voltage per element @I _F = 1.0A	V _{FM}	0.95		1.25	1.7	V
Peak Reverse Current @T _A = 25°C	I _{RM}	5.0				μA
At Rated DC Blocking Voltage @T _A = 125°C		500				
Reverse Recovery Time (Note 4)	t _{rr}	35				nS
Typical Junction Capacitance per leg (Note 3)	C _j	13				pF
Typical Thermal Resistance per leg (Note 1)	R _{θJA} R _{θJL}	62.5 25				°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150				°C

Note: 1. Mounted on glass epoxy PC board with 1.3mm² solder pad.
2. Mounted on aluminum substrate PC board with 1.3mm² solder pad.
3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
4. Measured with I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A. See figure 5.